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SILICON FILM (54) MANUFACTURE OF

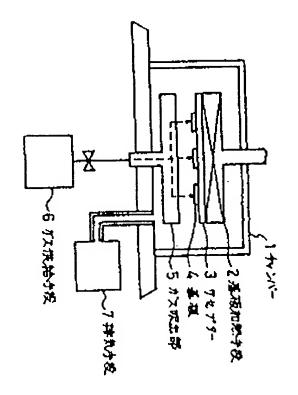
(57) Abstract:

deposition rate and excellent electric silicon film having a sufficient characteristics by a method wherein a PURPOSE: To form an amorphous

thermal CVD method is performed at the substrate temperature of 480°C or below using trisilane or higher silanes.

of a heating means 2, a susceptor 3, a gas blow- out hole 5, the exhaust hole been stabilized, raw gas is introduced, chamber 1 in advance, and after the atmospheric gas is introduced into the decomposition reaction. At this time, of the substrate 4 by thermal silicon film is formed on the surface chamber 1. As a result, an amorphous silane of high order which is higher exhaust means 7, they are placed on and the like connected to a gas inserted into the chamber 1 consisting consisting of a wafer and the like is substantially by performing a thermal and the temperature variation when a temperature of the substrate 4 has than trisilane is introduced into the thereabout by a heating means 2, the the upper surface of the susceptor 3. film is formed can be made small When they are heated up to 400°C or CONSTITUTION: The substrate 4

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